



Patent Application No. 10/657,505  
Customer Number: 42717

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chii-Ming Wu

Serial No.: 10/657,505

Filing Date: September 8, 2003

For: METHOD OF MANUFACTURING A CONTACT  
INTERCONNECTION LAYER CONTAINING  
A METAL AND NITROGEN BY ATOMIC  
LAYER DEPOSITION FOR DEEP SUB-MICRON  
SEMICONDUCTOR TECHNOLOGY

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Docket No.: 24061.406  
(TSMC2001-1247)

Examiner: Kennedy, Jennifer M.

Art Unit: 2812

RESPONSE TO RESTRICTION REQUIREMENT

Mail Stop: Amendment  
Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action mailed March 10, 2005, applicant hereby elects the embodiment represented by Figs. 2a-2c and Fig. 3. Applicant also elects Group A-1 ( $\text{Ti}(\text{OCH}(\text{CH}_3)_2)_4$ ); Group B-1 (Silicon gas source); Group C-1 (MN); and Group D-1 (CMP).

Applicant's election is made with traverse on the grounds that the embodiments delineated by the examiner are not patentably distinct and therefore constitute a single invention concept.

An early action on the merits is respectfully requested.

Respectfully submitted,

*T. F. Bliss*

Timothy F. Bliss  
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Date: 4/11/05

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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Mail Stop: Amendment, Commissioner For Patents, PO Box 1450, Alexandria, VA 22313-1450 on the date below.

Name

Date

*Gayle Connor*  
4-11-05